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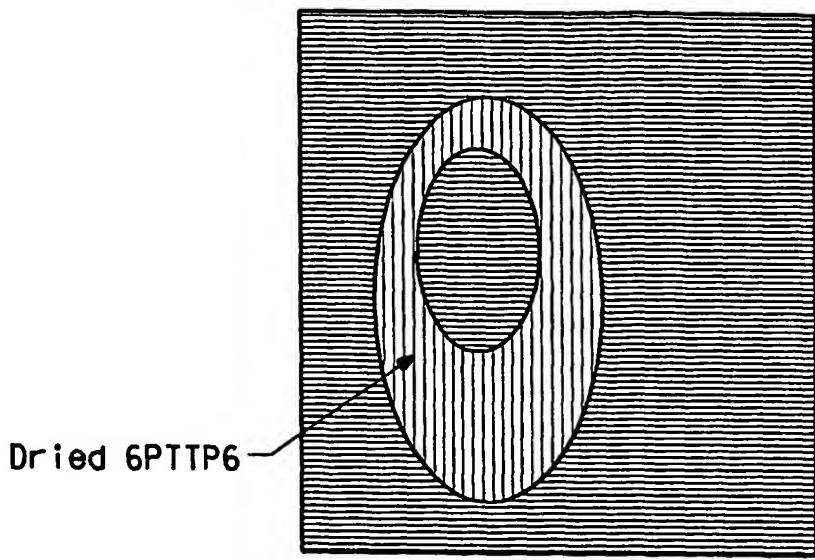
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- (71) Applicant (*for all designated States except US*): **E.I. DUPONT DE NEMOURS AND COMPANY [US/US]; 1007 MARKET STREET, WILMINGTON, DE 19898 (US).**
- (72) Inventor; and
- (75) Inventor/Applicant (*for US only*): **MALAJOVICH, Irina [US/US]; 110 Guernsey Road, Swathmore, PA 19081 (US).**
- (74) Agent: **SIEGELL, Barbara, C.; E. I. DU PONT DE NEMOURS AND COMPANY, LEGAL PATENT RECORDS CENTER, 4417 Lancaster Pike, Wilmington, DE 19805 (US).**
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(54) Title: LAMINATION OF ORGANIC SEMICONDUCTORS



(57) Abstract: Low temperature, ambient pressure processes are desired for fabrication of transistors on flexible polymer substrates. Lamination of semiconductors is such a process. The semiconductor is deposited on a donor substrate. The donor is positioned over a receiver substrate, which may be patterned with additional transistor elements. The semiconductor is transferred from the donor to the receiver by lamination.

WO 2005/011016 A2



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